

ABSTRACT OF THE DISCLOSURE

A planarization method using anisotropic etching can be applied to planarize an insulating layer with an uneven surface on a substrate. H_2SO_4 , H_3PO_4 , HF and H_2O are mixed to form an etching solution. The substrate is placed into the etching solution to make the etching solution pass the surface of the insulating layer at a flow rate to etch the insulating layer. After a period of etching time, the insulating layer with a more planar surface can be obtained.

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